



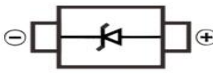
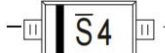
安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SD103AT

SOD-523 Schottky Barrier Diode 肖特基势垒二极管

Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	SD103AT
Pin 管脚	
Mark 打标	

Absolute Maximum Ratings 最大额定值

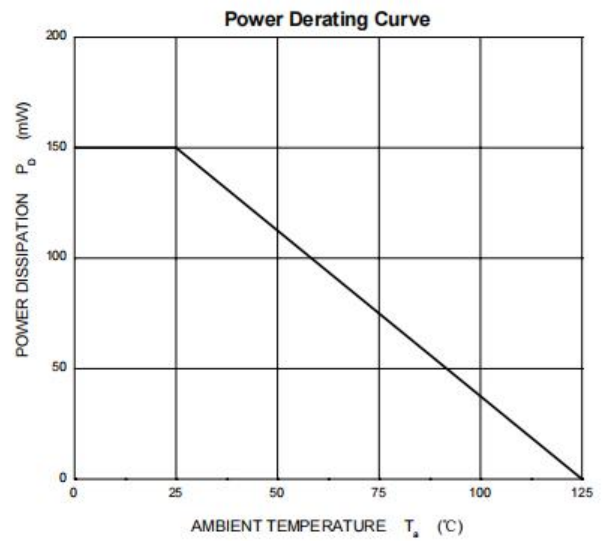
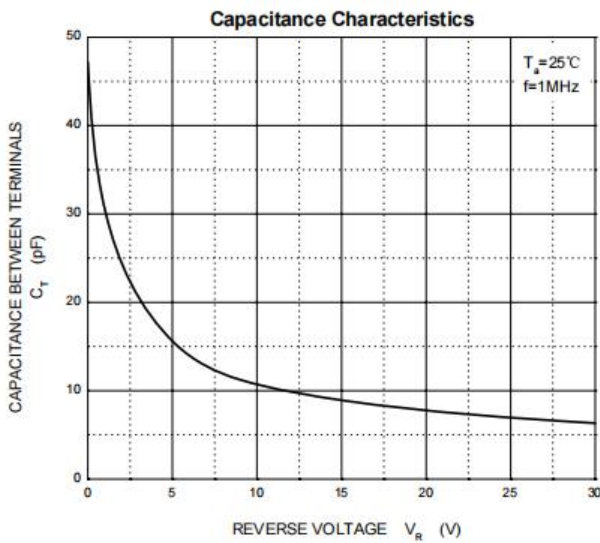
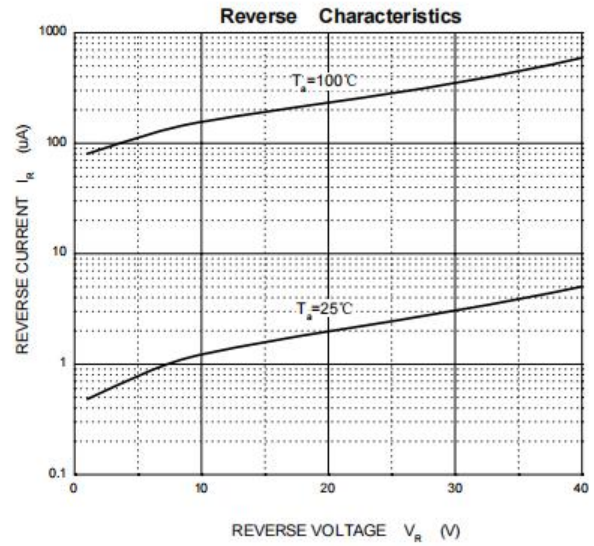
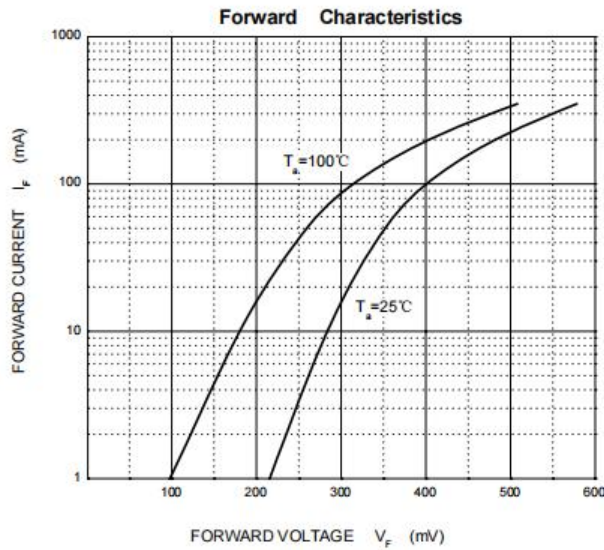
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Reverse Voltage 反向峰值电压	V_R	40	V
Repetitive Reverse Voltage 重复反向电压	V_{RRM}	40	V
Reverse Work Voltage 反向工作电压	V_{RWM}	40	V
RMS Reverse Voltage 反向电压均方根值	$V_R(RMS)$	28	V
Forward Work Current 正向工作电流	I_O	350	mA
Peak Forward Surge Current 正向峰值浪涌电流	I_{FSM}	2000	mA
Power dissipation 耗散功率	$P_D(T_A=25^\circ C)$	150	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	668	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+125 $^\circ C$	

Electrical Characteristics 电特性

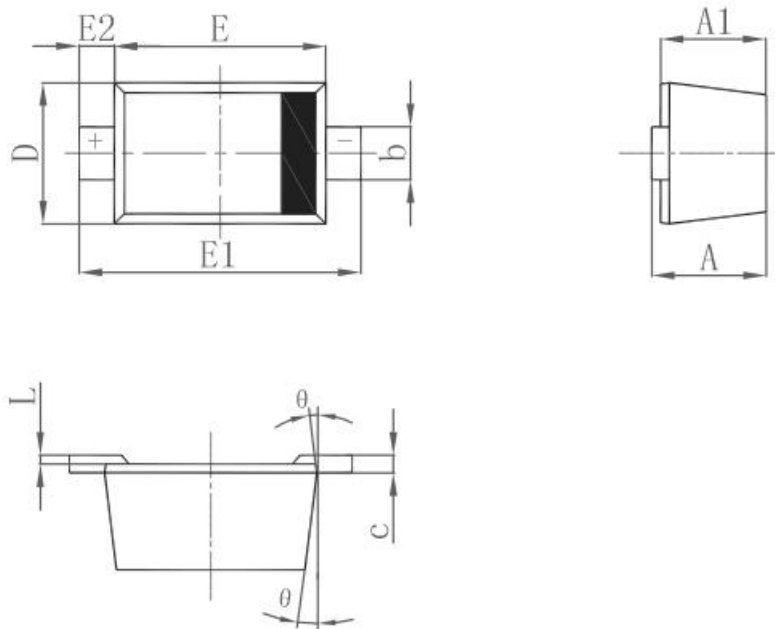
($T_A=25^\circ C$ unless otherwise noted 如无特殊说明, 温度为 $25^\circ C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=100\mu A$)	$V_{(BR)}$	40	—	V
Reverse Leakage Current($V_R=10V$) 反向漏电流($V_R=20V$) ($V_R=30V$)	I_R	—	1 2 5	μA
Forward Voltage($I_F=20mA$) 正向电压($I_F=200mA$)	V_F	—	0.37 0.6	V
Diode Capacitance 二极管电容($V_R=0V, f=1MHz$)	C_D	—	50	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	10	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200 REF		0.008 REF	
L	0.010	0.070	0.001	0.003
θ	7° REF		7° REF	

单击下面可查看定价，库存，交付和生命周期等信息

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